

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

The **ASI 1010** is Designed for General Purpose Class C Power Amplifier Applications up to 1500 MHz.

**FEATURES:**

- $P_G = 12$  dB min. at 10 W/ 1,000 MHz
- Hermetic Microstrip Package
- **Omnigold™** Metalization System

**MAXIMUM RATINGS**

$I_C$	1.0 A
$V_{CC}$	35 V
$P_{DISS}$	29 W @ $T_C = 25^\circ C$
$T_J$	$-65^\circ C$ to $+200^\circ C$
$T_{STG}$	$-65^\circ C$ to $+200^\circ C$
$\theta_{JC}$	8.5 $^\circ C/W$

**PACKAGE STYLE .250 2L FLG**

DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.028 / 0.71	.032 / 0.81
B	.740 / 18.80	
C	.245 / 6.22	.255 / 6.48
D	.128 / 3.25	.132 / 3.35
E	.125 / 3.18	
F	.110 / 2.79	.117 / 2.97
G	.117 / 2.97	
H	.560 / 14.22	.570 / 14.48
I	.790 / 20.07	.810 / 20.57
J	.225 / 5.72	.235 / 5.97
K	.165 / 4.19	.185 / 4.70
L	.003 / 0.08	.007 / 0.18
M	.058 / 1.47	.068 / 1.73
N	.119 / 3.02	.135 / 3.43
P	.149 / 3.78	.187 / 4.75

**ORDER CODE: ASI10525**

**CHARACTERISTICS**  $T_C = 25^\circ C$ 

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
$BV_{CBO}$	$I_C = 1.0$ mA	45			V
$BV_{CER}$	$I_C = 10$ mA $R_{BE} = 10 \Omega$	45			V
$BV_{EBO}$	$I_E = 1.0$ mA	3.5			V
$I_{CBO}$	$V_{CB} = 28$ V			2.5	mA
$h_{FE}$	$V_{CE} = 5.0$ V $I_C = 500$ mA	15		120	---
$C_{ob}$	$V_{CB} = 28$ V $f = 1.0$ MHz			10	pF
$P_G$ $\eta_c$	$V_{CC} = 28$ V $P_{OUT} = 10$ W $f = 1.0$ GHz	12 50			dB %